



LAPD-2-09-17-CHIP

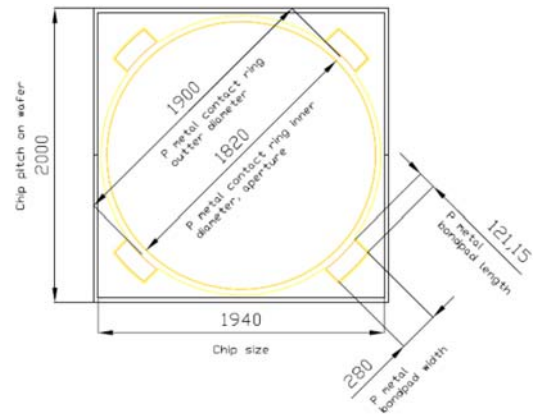


TECHNICAL DATA

Photodiode Chip die

InGaAs

LAPD-2-09-17-CHIP adopt InGaAs pin structure based on InP by MOCVD method and planar diffusing technology. The active area is Ø 2 mm respectively.



Absolute Maximum Ratings

Item	Symbol	Value	Unit
Reverse Voltage	U_R	20	V
Reverse Current	I_R	20	mA
Forward current	I_F	10	mA
Operating Temperature	T_{opr}	-20 ... +85	°C
Storage Temperature	T_{stg}	-40 ... +85	°C

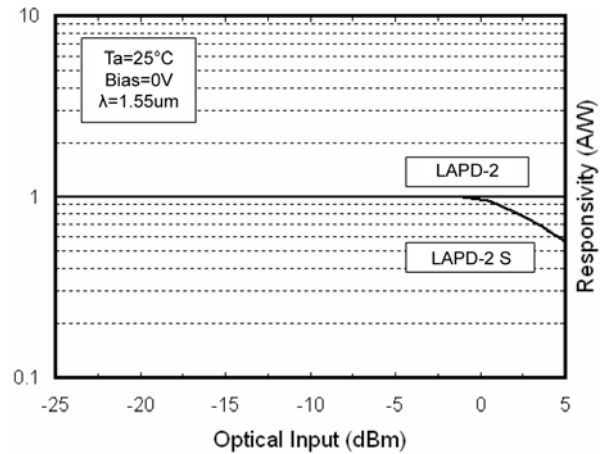
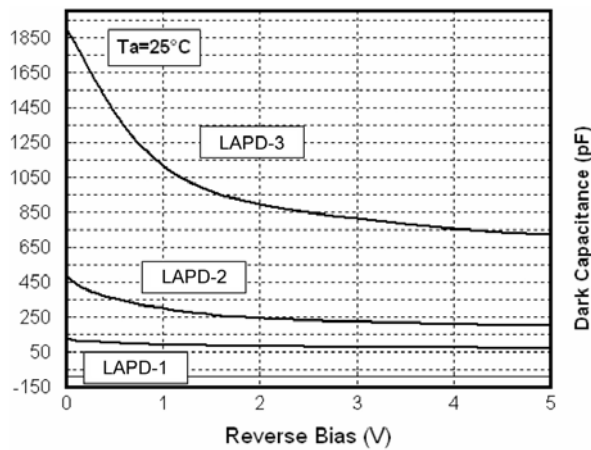
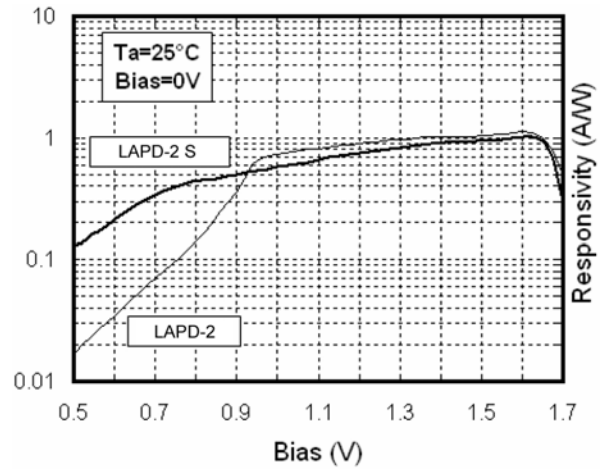
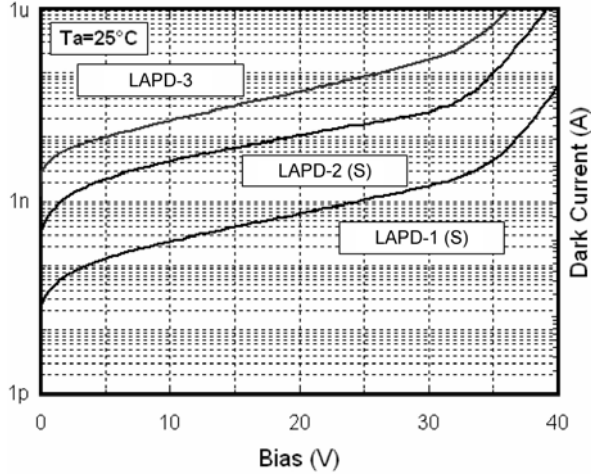
Specifications

Item	Min.	Typ.	Max.	Unit
Wavelength Range	0.9 .. 1.7			µm
Active Area	Ø 2			mm
Saturation Power	1550 nm	-	2	dBm
Specific Detectivity (D^*)	1550 nm	2.5	5	10^{12} Jones
Responsibility (0 V)	650 nm	0.02	0.05	A/W
	850 nm	0.10	0.20	
	1310 nm	0.80	0.90	
	1550 nm	0.85	0.95	
Capacitance	0 V	-	500	pF
	-5 V	-	250	
Dark Current	-5 V	-	10	nA
Shunt Resistance	6	25	-	MΩ
Chip Size	1940 x 1940			µm
Chip Thickness	300			µm

Packing: Chips on adhesive film



Typical Performance Curves



LAPD-2 Spatial Response
 $T_a = 25^\circ\text{C}$, Bias = 0V, $\lambda = 1550\text{nm}$

